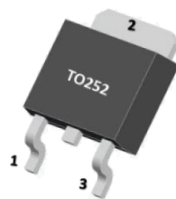


DESCRIPTION

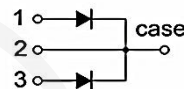
The MBR20150CT meet the ROHS and Green Product requirement with full function reliability approved.

FEATURE

- *Schottky Barrier Chip
- *Guard Ring Die Construction for Transient Protection
- *Low Power Loss,High Efficiency
- *High Surge Capability
- *High Current Capability and Low Forward Voltage Drop
- *For Use in Low Voltage, High Frequency Inverters,Free Wheeling, and Polarity Protection Applications



1. ANODE
2. CATHODE
3. ANODE



ABSOLUTE MAXIMUM RATINGS(TA=25°C, unless otherwise specified.)

SYMBOL	PARAMETER	VALUE	UNIT
VRRM	Peak repetitive reverse voltage	150	V
VRWM	Working peak reverse voltage	150	V
VR	DC blocking voltage	150	V
VR(RMS)	RMS reverse voltage	105	V
IO	Average rectified output current	20 (10*2)	A
IFSM	Non-Repetitive peak forward surge current	150*2	A
Tj	Junction temperature	175	°C
Tstg	Storage temperature	-55 ~ +150	°C
Cj (Ctot)	Typical total capacitance VR=5V,f=1MHz	500	pF
RθJA	Thermal Resistance from Junction to Ambient	100	°C/W
RθJC	Thermal Resistance From Junction To Case	5	°C/W

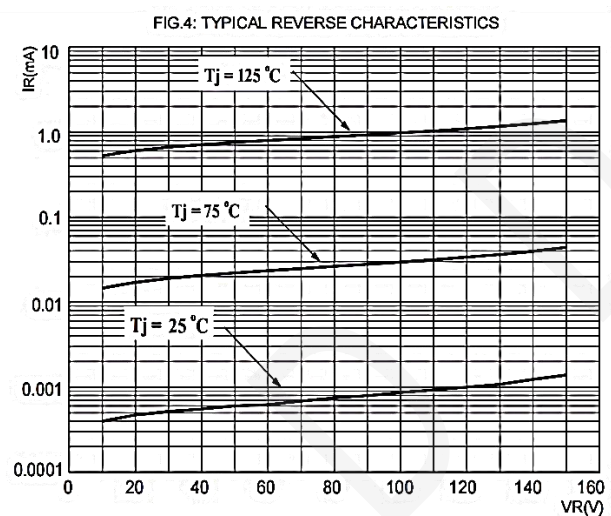
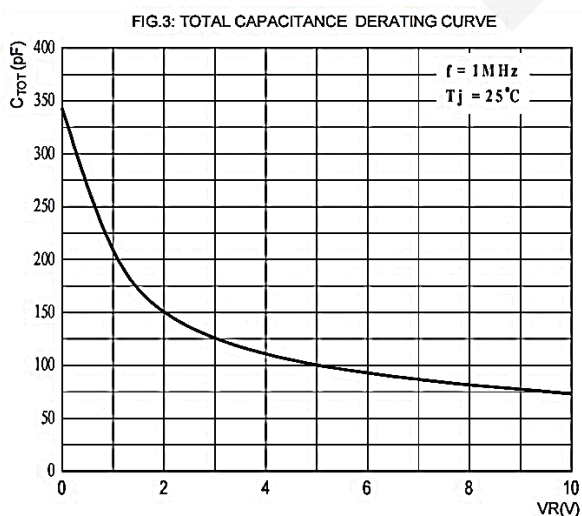
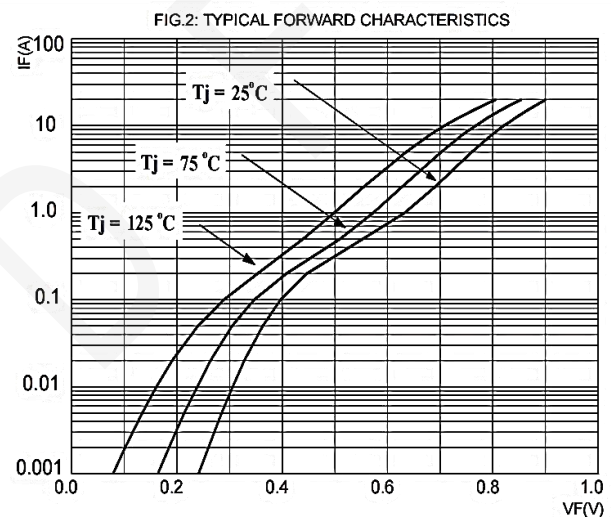
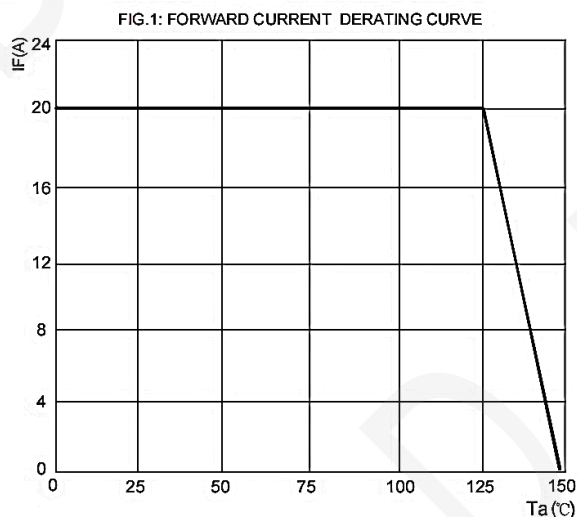
Notes: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (TA=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse voltage	V(BR)	IR=0.1mA	150			V
Reverse current	IR	VR=150V	Tj =25°C	0.5	5	uA
			Tj =125°C	2.0		mA
Forward voltage	VF	IF=5A	Tj =25°C	0.76		V
			Tj =125°C	0.64		V
		IF=10A	Tj =25°C	0.83	0.90	V
			Tj =125°C	0.71		V

Pulse test: pulse width ≤300μs, duty cycles ≤ 2.0%.

■ TYPICAL CHARACTERISTICS



TO - 252 Package Outline Dimensions

